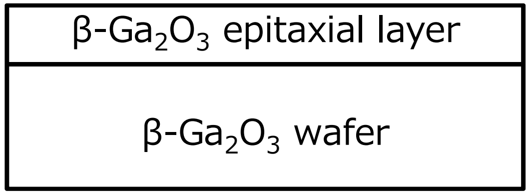
Standard specifications of 100 mm β-Ga_2O_3 epitaxial wafer (by HVPE)

Epitaxial layer

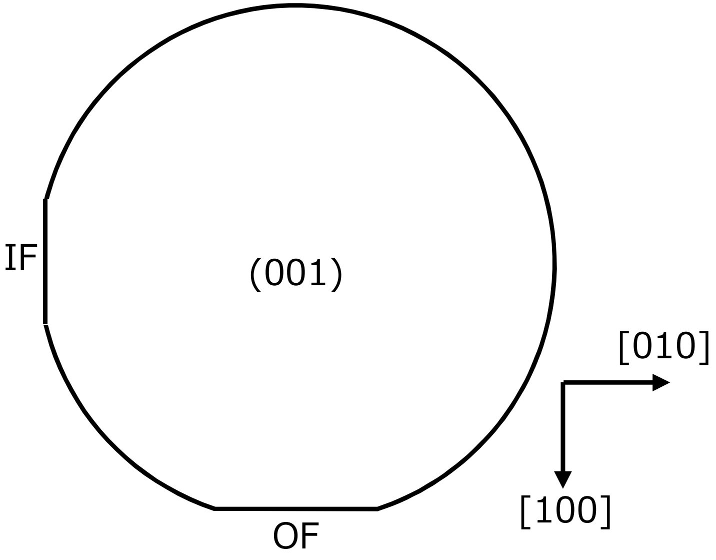
Items	Specifications
Dopant	Si (n-type)
Doping concentration *A value can be selected in increments of 1×10^{16} cm^{-3}.	Specify a value in the range between 1×10^{16} and 9×10^{16} cm^{-3}
Thickness *A value can be selected in increments 1 μm.	Specify a value in the range between 5 and 10 μm



Cross section of β-Ga_2O_3 epitaxial wafer

Wafer

Items	Specifications
Dopant	Sn (n-type)
Doping concentration	Using the range of $1\times10^{18} \sim 2\times10^{19}$ cm^{-3}
Orientation	(001)
Size	100 mm
Thickness	0.65 mm
XRD FWHM	≦350 arcsec
Off set angle	0°±1°



Orientation

Remarks
1 These products must be used for research and development purposes only.
2 The substrates must not be used as a seed crystal.
3 The specifications are subject to change without notice.

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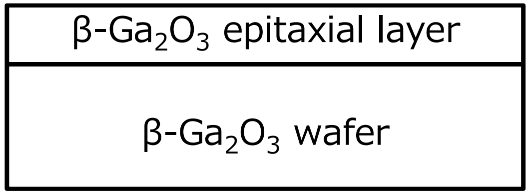
Standard specifications of 2 inch β-Ga_2O_3 epitaxial wafer (by HVPE)

Epitaxial layer

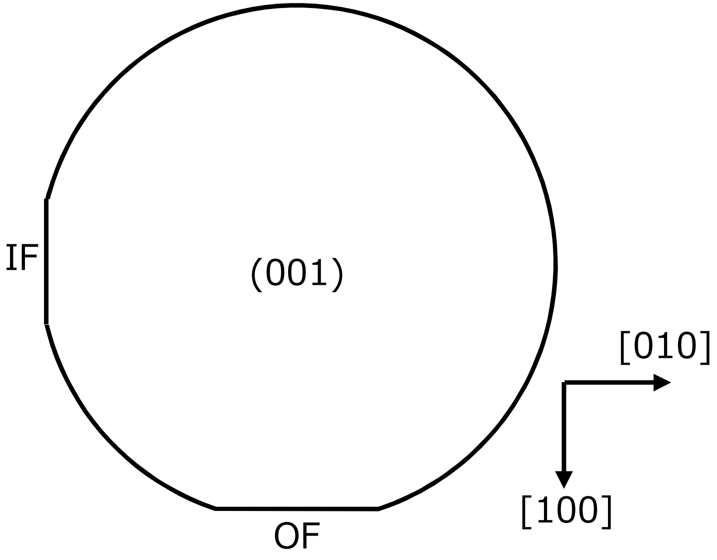
Items	Specifications
Dopant	Si (n-type)
Doping concentration *A value can be selected in increments of 1×10^{16} cm^{-3} .	Specify a value in the range between 1×10^{16} and 9×10^{16} cm^{-3}
Thickness *A value can be selected in increments 1 μm.	Specify a value in the range between 5 and 10 μm



Cross section of β-Ga_2O_3 epitaxial wafer

Wafer

Items	Specifications
Dopant	Sn (n-type)
Doping concentration	Using the range of $1\times10^{18}\sim2\times10^{19}$ cm^{-3}
Orientation	(001)
Size	2 inch
Thickness	0.65 mm
XRD FWHM	≦350 arcsec
Off set angle	0°±1°



Orientation

Remarks
1 These products must be used for research and development purposes only.
2 The substrates must not be used as a seed crystal.
3 The specifications are subject to change without notice.

Novel Crystal Technology, Inc.

2022.11.22